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Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET



Marking Code: 90YXX

PRODUCT SUMMARY				
V _{DS} (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.024			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.032			
I _D (A)	8			
Configuration	Single			

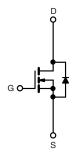
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rg and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



N-Channel	MOSEET

ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2348CES (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	30	V	
Gate-source voltage		V _{GS}	± 20	V	
Continuous drain current	T _C = 25 °C ^a	- In I	8		
Continuous drain current	T _C = 125 °C		5.3		
Continuous source current (diode conduction	I _S	3.8	А		
Pulsed drain current ^b	I _{DM}	32			
Single pulse avalanche current	L = 0.1 mH	I _{AS}	15.5		
Single pulse avalanche energy	L = 0.1 mn	E _{AS}	12	mJ	
Maximum power dissipation	T _C = 25 °C	P _D	3	W	
	T _C = 125 °C		1	VV	
Operating junction and storage temperature	T _J , T _{stg}	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB Mount c	R_{thJA}	166	°C/W	
Junction-to-foot (drain)	ion-to-foot (drain)		50	C/VV	

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static		•		l		ı		
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30		-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	· V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 30 V	-	=.	1		
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μA	
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	150		
On-state drain current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	10	=.	-	Α	
		V _{GS} = 10 V	I _D = 12 A	-	0.020	0.024		
Drain actives an etata registance 8	В	V _{GS} = 10 V	I _D = 12 A, T _J = 125 °C	-	-	0.036		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 12 A, T _J = 175 °C	-	-	0.042	Ω	
		V _{GS} = 4.5 V	I _D = 8 A	-	0.026	0.032		
Forward transconductance b	9 _{fs}	V _{DS}	= 15 V, I _D = 3 A	-	12	-	S	
Dynamic ^b								
Input capacitance	C _{iss}			-	450	540		
Output capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$	-	95	125	pF	
Reverse transfer capacitance	C _{rss}			-	39	50		
Total gate charge ^c	Qg			-	8.15	14.5		
Gate-source charge ^c	Q_{gs}	V _{GS} = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 5.5 \text{ A}$	-	1.65	-	nC	
Gate-drain charge ^c	Q _{gd}			-	1.25	-		
Gate resistance	R_g		f = 1 MHz		13	27	Ω	
Turn-on delay time ^c	t _{d(on)}			-	6	7		
Rise time ^c	t _r	V _{DD} =	$V_{DD} = 15 \text{ V}, R_{I} = 3.4 \Omega$		4	12	1	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong 4.4 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	18	32	ns	
Fall time ^c	t _f			-	4	9		
Source-Drain Diode Ratings and Charact	eristics ^b							
Pulsed current ^a	I _{SM}			-	-	32	Α	
Forward voltage	V_{SD}	I _F = 3.5 A, V _{GS} = 0 V		-	0.81	1.2	V	
Body diode reverse recovery time	t _{rr}			-	10	20	ns	
Body diode reverse recovery charge	Qrr	I _F = 4 A, di/dt = 100A/us		-	5	10	nC	
Reverse recovery fall time	t _a			-	7	-		
Reverse recovery rise time	t _b			-	3	-	ns	
Body diode peak reverse recovery current	I _{RM(REC)}			-	-0.98	-	Α	

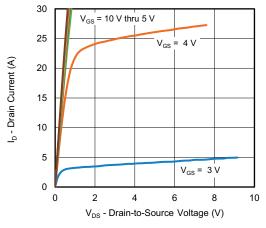
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

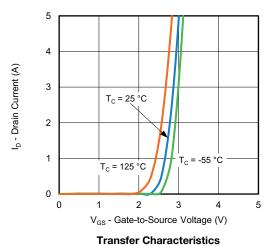
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



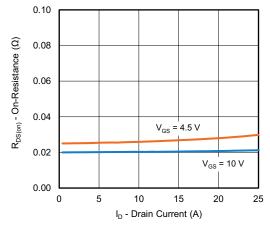
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



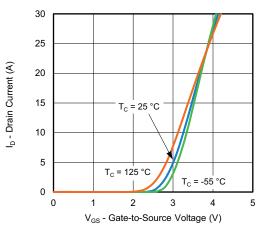
Output Characteristics



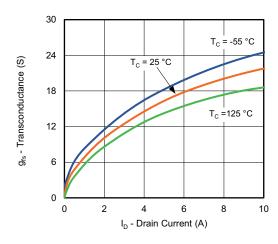




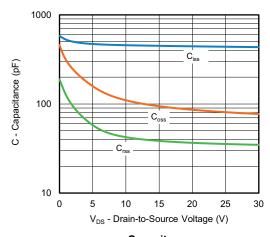
On-Resistance vs. Drain Current



Transfer Characteristics



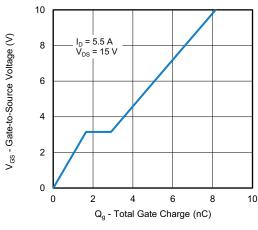
Transconductance



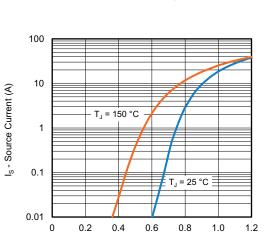
Capacitance



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

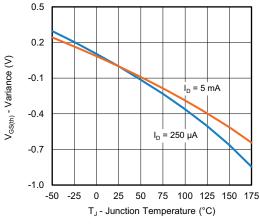


Gate Charge

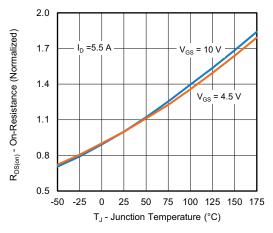


V_{SD} - Source-to-Drain Voltage (V) **Source Drain Diode Forward Voltage**

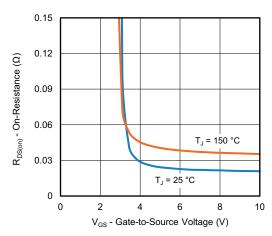
0.8



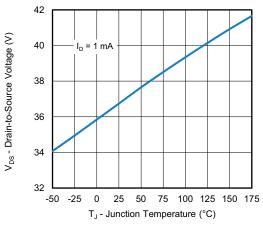
Threshold Voltage



On-Resistance vs. Junction Temperature



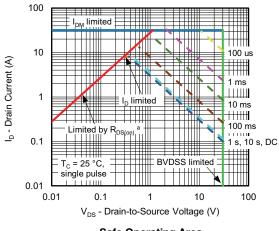
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



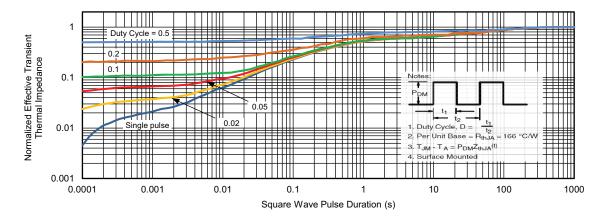
Safe Operating Area

Note

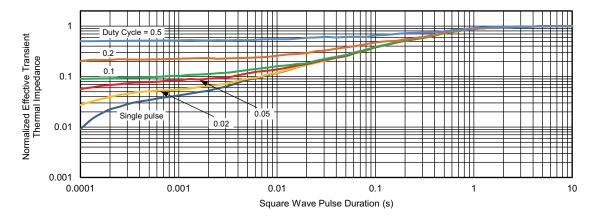
a. $V_{GS} > \mbox{minimum} \ V_{GS}$ at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62082.



SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90	1.90 BSC		8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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